

Application No.: 10/801,884

Docket No.: JCLA12524

REMARKSPresent Status of the Application

The Office Action rejected claims 12-14 and 16-18 under 35 U.S.C. 102(e), as being anticipated by Kawano (U.S. 6,759,345). Claim 15 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Applicant has amended claim 12 to more clearly define the present invention. The amendment in the claim 12 is as shown in Fig. 6, and no new matter is entered. After entry of the foregoing amendments, claims 12-18 remain pending in the present application, and reconsideration of those claims is respectfully requested.

Rejection under 35 U.S.C 102 (e)

*Applicant respectfully traverses the 102(e) rejection of claims 12-14 and 16-18 because Kawano (U.S. 6,759,345) does not teach every element recited in these claims.*

In order to properly anticipate Applicants' claimed invention under 35 U.S.C 102, each and every element of claim in issue must be found, "either expressly or inherently described, in a single prior art reference". "The identical invention must be shown in as complete details as is contained in the .... claim. Richardson v. Suzuki Motor Co., 868 F. 2d 1226, 1236, 9 USPQ2d 1913, 1920 (Fed. Cir. 1989)." See M.P.E.P. 2131, 8<sup>th</sup> ed., 2001.

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The present invention is in general related a correction pattern for a chemical-mechanical polishing proximity correct as claim 12 recites:

Claim 12. A correction pattern for a chemical-mechanical polishing proximity correct, comprising:

a polish area over a wafer, wherein the polish area has a plurality of boundaries and at least a corner;

a protective region set up outside the polish area;

a shadow area set up between the polish area and the protection region, wherein the shadow area at least comprises:

*a plurality of peripheral sections set up along the boundaries of the polish area, wherein the peripheral sections have a first width; and*

*at least a corner section set up along the corner of the polish area, wherein the corner section connects the adjacent peripheral sections, and the corner section has a second width such that the second width is greater than the first width.*

The Office Action stated Figs. 26-31 of the Kawano reference have disclosed claims 12-14 and 16-18 of the present application. However, applicant does not agree. This is because Kawano fails to disclose, teach or suggest the shadow area including a plurality of peripheral sections and at least a corner section as recited in claim 12, in particular, the peripheral sections are set up along the boundaries of the polish area and have a first width, the corner section is set up along the corner of the polish area and connects the adjacent peripheral sections, and the corner section has a second width larger than the first width.

In the Kawano reference, the peripheral area 306 is around the effective device area 302, and the grid line 304 is positioned between the chips formed in the effective device area 302 (as shown in Figs. 26 and 27), wherein a silicon nitride film 308 and a silicon oxide layer 310 are formed in the areas 302, 304 and 306. Next, as shown in Figs. 28 and 29, a photoresist layer is formed to cover the entire effective device area 302, the grid line 304 and a portion of the

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peripheral area 306 surrounding the effective device area 302. In other words, the photoresist layer only extends a distance D beyond the grid line 304 into the peripheral area 106 (see col. 5, lines 1-4). Thereafter, as shown in Figs. 30 and 31, an etching step is performed by using the photoresist layer 312 as a mask to remove a portion of the silicon oxide layer 310 in the peripheral area 306, such that the region A of the peripheral area 306 has the silicon oxide layer 310 and the silicon nitride film 308 therein and the region B of the peripheral area 306 only has the silicon nitride film 308 therein. In particular, the region A surrounding the effective device area 302 *has the same width at the corner portion and the linear portion*. The region B does not have the corner portion and the linear portion.

FIG.30

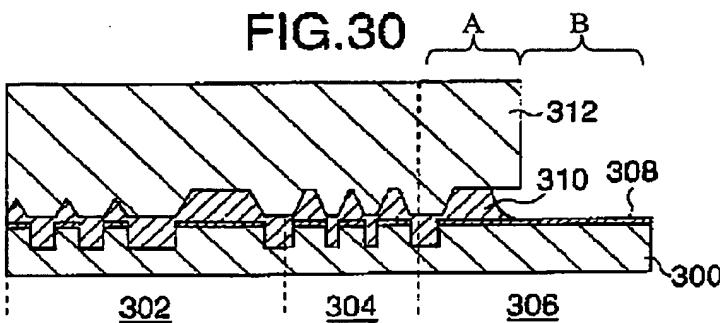
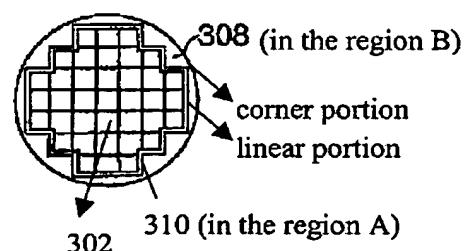


FIG.31



Therefore, Kawano fails to teach there are a plurality of peripheral sections along the boundaries of the polish area and at least a corner section along the corner of the polish area and connecting two adjacent peripheral sections, wherein *the peripheral sections have a first width and the corner section has a second width larger than the first width*.

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For at least the foregoing reasons, Applicant respectfully submits Kawano does not teach each and every element in claim 12. Independent claim 12 patently defines over the prior art reference, and should be allowed. For at least the same reasons, dependent claims 13-18 patently define over the prior art as a matter of law, for at least the reason that these dependent claims contain all features of their respective independent claim.

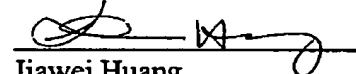
### CONCLUSION

For at least the foregoing reasons, it is believed that the pending claims are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

Respectfully submitted,  
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